NPN RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AM1011-500** is a Common Base Device Designed for Pulsed L-Band Radar Amplifier Applications.

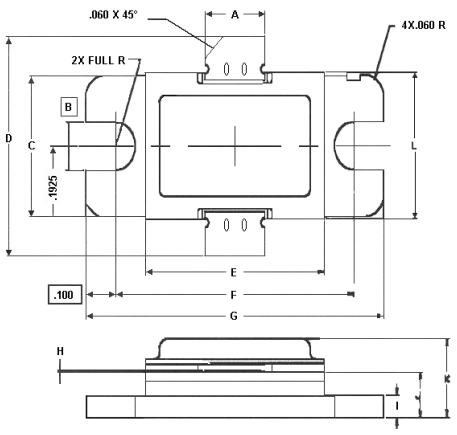
FEATURES INCLUDE:

- Input/Output Matching
- Gold Metallization
- Hermetic Metal/Ceramic Package

MAXIMUM RATINGS

I_C	27 A
V_{CBO}	55 V
P_{DISS}	1360 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to+200 ^{O}C
T_{STG}	-65 ^{O}C to+200 ^{O}C
θ_{JC}	0.11 ^{O}C/W

PACKAGE STYLE 400 X 600 2L FLG



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.195/4.95	.205/5.21
B	.130/3.30	
C	.380/9.65	.390/9.91
D	.570/14.48	
E	.593/15.06	.607/15.42
F	.790/20.07	.810/20.57
G	.995/25.27	1.005/25.53
H	.002/0.05	.006/0.15
I	.055/1.40	.065/1.65
J	.110/2.79	.130/3.30
K		.230/5.84
L	.393/9.98	.407/10.34

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 50 mA	70			V
BV_{CES}	I_C = 50 mA	70			V
I_{CES}	V_{CE} = 50 V			40	mA
BV_{EBO}	I_E = 30 mA	3.0			V
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	10		200	---
P_G	V_{CE} = 50 V P_{OUT} = 500 W f = 1090 MHz	8.5	8.5		dB
η_C	Pulse Width = 32 μS Duty Cycle = 2%	40	35		%

Specifications are subject to change without notice.